

**MOTOROLA  
SEMICONDUCTOR  
TECHNICAL DATA**

**8-Bit Serial-Input/Serial- or  
Parallel-Output Shift Register  
with Latched 3-State Outputs  
High-Performance Silicon-Gate CMOS**

The MC54/74HC595 is identical in pinout to the LS595. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LS-TTL outputs.

The HC595 consists of an 8-bit serial shift register and an 8-bit D-type latch with three-state parallel outputs. The shift register accepts serial data and provides a serial output. The shift register also provides parallel data to the 8-bit latch. The shift register and latch have independent clock inputs. This device also has an asynchronous reset for the shift register.

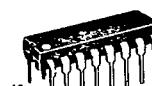
The HC595 directly interfaces with the Motorola SPI serial data port on CMOS MPUs and MCUs.

- Output Drive Capability: 15 LS-TTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1  $\mu$ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 328 FETs or 82 Equivalent Gates

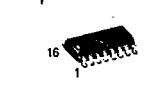
**MC54/74HC595**



J SUFFIX  
CERAMIC  
CASE 620-09



N SUFFIX  
PLASTIC  
CASE 648-06



D SUFFIX  
SOIC  
CASE 751B-03

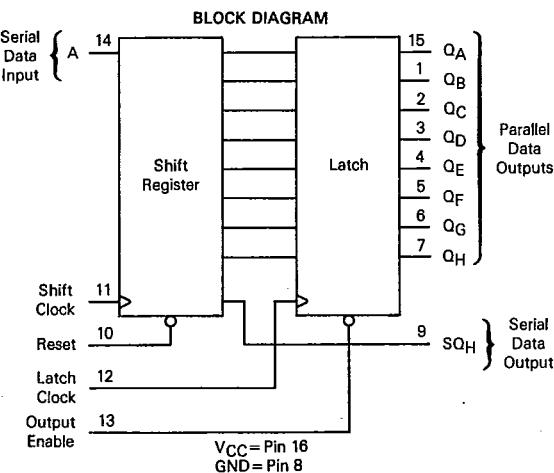
**ORDERING INFORMATION**

MC74HCXXXN	Plastic
MC54HCXXXJ	Ceramic
MC74HCXXXD	SOIC

$T_A = -55^\circ$  to  $125^\circ\text{C}$  for all packages.  
Dimensions in Chapter 7.

**PIN ASSIGNMENT**

Q <sub>B</sub>	1	16	VCC
Q <sub>C</sub>	2	15	QA
Q <sub>D</sub>	3	14	A
Q <sub>E</sub>	4	13	Output Enable
Q <sub>F</sub>	5	12	Latch Clock
Q <sub>G</sub>	6	11	Shift Clock
Q <sub>H</sub>	7	10	Reset
GND	8	9	SO <sub>H</sub>



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## MC54/74HC595

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V <sub>In</sub>	DC Input Voltage (Referenced to GND)	-1.5 to V <sub>CC</sub> +1.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
I <sub>out</sub>	DC Output Current, per Pin	±35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±75	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic or Ceramic DIP or SOIC Package	750 500	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>In</sub> and V<sub>out</sub> should be constrained to the range GND ≤ V<sub>In</sub> or V<sub>out</sub> ≤ V<sub>CC</sub>. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

\*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

t<sub>Derating</sub> — Plastic DIP: -10 mW/°C from 65° to 125°C

Ceramic DIP: -10 mW/°C from 100° to 125°C

SOIC Package: -7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 4.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
V <sub>In</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V	
T <sub>A</sub>	Operating Temperature, All Package Types	-55	+125	°C	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	V <sub>CC</sub> =2.0 V V <sub>CC</sub> =4.5 V V <sub>CC</sub> =6.0 V	0 0 0	1000 500 400	ns

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				25°C to -55°C	≤85°C	≤125°C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>out</sub> =0.1 V or V <sub>CC</sub> -0.1 V  I <sub>out</sub>  ≤20 μA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> =0.1 V or V <sub>CC</sub> -0.1 V  I <sub>out</sub>  ≤20 μA	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
V <sub>OH</sub>	Minimum High-Level Output Voltage, Q <sub>A</sub> -Q <sub>H</sub>	V <sub>In</sub> =V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>  ≤20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V <sub>In</sub> =V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>  ≤6.0 mA  I <sub>out</sub>  ≤7.8 mA	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	
V <sub>OL</sub>	Maximum Low-Level Output Voltage, Q <sub>A</sub> -Q <sub>H</sub>	V <sub>In</sub> =V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>  ≤20 μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V <sub>In</sub> =V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>  ≤6.0 mA  I <sub>out</sub>  ≤7.8 mA	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	

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## DC ELECTRICAL CHARACTERISTICS (Continued)

Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	Guaranteed Limit			Unit
				25°C to -55°C	≤85°C	≤125°C	
V <sub>OH</sub>	Minimum High-Level Output Voltage, S <sub>QH</sub>	$V_{in}=V_{IH}$ or $V_{IL}$ $ I_{out}  \leq 20 \mu A$	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
V <sub>OL</sub>	Maximum Low-Level Output Voltage, S <sub>QH</sub>	$V_{in}=V_{IH}$ or $V_{IL}$ $ I_{out}  \leq 20 \mu A$	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
V <sub>IL</sub>	Maximum Low-Level Output Voltage, S <sub>QH</sub>	$V_{in}=V_{IH}$ or $V_{IL}$ $ I_{out}  \leq 4.0 \text{ mA}$ $ I_{out}  \leq 5.2 \text{ mA}$	2.0	0.1	0.1	0.1	V
			4.5	0.26	0.33	0.40	
I <sub>in</sub>	Maximum Input Leakage Current	$V_{in}=V_{CC}$ or GND	6.0	±0.1	±1.0	±1.0	μA
			—	—	—	—	
I <sub>OZ</sub>	Maximum Three-State Leakage Current, Q <sub>A</sub> -Q <sub>H</sub>	Output in High-Impedance State $V_{in}=V_{IL}$ or $V_{IH}$ $V_{out}=V_{CC}$ or GND	6.0	±0.5	±5.0	±10.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in}=V_{CC}$ or GND $I_{out}=0 \mu A$	6.0	8	80	160	μA

NOTE: Information on typical parametric values can be found in Chapter 4.

AC ELECTRICAL CHARACTERISTICS (C<sub>L</sub>=50 pF, Input t<sub>r</sub>=t<sub>f</sub>=6 ns)

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			25°C to -55°C	≤85°C	≤125°C	
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 7)	2.0	6.0	4.8	4.0	MHz
		4.5	30	24	20	
		6.0	35	28	24	
t <sub>PLH</sub> / t <sub>PHL</sub>	Maximum Propagation Delay, Shift Clock to S <sub>QH</sub> (Figures 1 and 7)	2.0	210	265	315	ns
t <sub>PHL</sub>	Maximum Propagation Delay, Reset to S <sub>QH</sub> (Figures 2 and 7)	2.0	175	220	265	ns
		4.5	35	44	53	
		6.0	30	37	45	
t <sub>PLH</sub> / t <sub>PHL</sub>	Maximum Propagation Delay, Latch Clock to Q <sub>A</sub> -Q <sub>H</sub> (Figures 3 and 7)	2.0	175	220	265	ns
t <sub>PLZ</sub> / t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Q <sub>A</sub> -Q <sub>H</sub> (Figures 4 and 8)	2.0	150	190	225	ns
		4.5	30	38	45	
		6.0	26	33	38	
t <sub>PZL</sub> / t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Q <sub>A</sub> -Q <sub>H</sub> (Figures 4 and 8)	2.0	150	190	225	ns
t <sub>T LH</sub> / t <sub>T HL</sub>	Maximum Output Transition Time, Q <sub>A</sub> -Q <sub>H</sub> (Figures 3 and 7)	2.0	60	75	90	ns
		4.5	12	15	18	
		6.0	10	13	15	
t <sub>T LH</sub> / t <sub>T HL</sub>	Maximum Output Transition Time, S <sub>QH</sub> (Figures 1 and 7)	2.0	75	95	110	ns
C <sub>in</sub>	Maximum Input Capacitance	2.0	15	15	15	pF
		—	—	—	—	
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State), Q <sub>A</sub> -Q <sub>H</sub>	—	—	—	—	pF

## NOTES:

1. For propagation delays with loads other than 50 pF, see Chapter 4.
2. Information on typical parametric values can be found in Chapter 4.

CPD	Power Dissipation Capacitance (Per Package) Used to determine the no-load dynamic power consumption: $P_D = CPD V_{CC}^2 f + ICC V_{CC}$ For load considerations, see Chapter 4.	Typical @ 25°C, V <sub>CC</sub> =5.0 V		pF
		300	—	

## MOTOROLA HIGH-SPEED CMOS LOGIC DATA

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## MC54/74HC595

TIMING REQUIREMENTS (Input  $t_r = t_f = 6$  ns)

Symbol	Parameter	$V_{CC}$ V	Guaranteed Limit			Unit
			25°C to -55°C	≤ 85°C	≤ 125°C	
$t_{SU}$	Minimum Setup Time, Serial Data Input A to Shift Clock (Figure 5)	2.0	100	125	150	ns
		4.5	20	25	30	
		6.0	17	21	26	
$t_{SU}$	Minimum Setup Time, Shift Clock to Latch Clock (Figure 6)	2.0	100	125	150	ns
		4.5	20	25	30	
		6.0	17	21	26	
$t_h$	Minimum Hold Time, Shift Clock to Serial Data Input A (Figure 5)	2.0	5	5	5	ns
		4.5	5	5	5	
		6.0	5	5	5	
$t_{REC}$	Minimum Recovery Time, Reset Inactive to Shift Clock (Figure 2)	2.0	50	65	75	ns
		4.5	10	13	15	
		6.0	9	11	13	
$t_W$	Minimum Pulse Width, Reset (Figure 2)	2.0	80	100	120	ns
		4.5	16	20	24	
		6.0	14	17	20	
$t_W$	Minimum Pulse Width, Shift Clock (Figure 1)	2.0	80	100	120	ns
		4.5	16	20	24	
		6.0	14	17	20	
$t_W$	Minimum Pulse Width, Latch Clock (Figure 6)	2.0	80	100	120	ns
		4.5	16	20	24	
		6.0	14	17	20	
$t_r, t_f$	Maximum Input Rise and Fall Times (Figure 1)	2.0	1000	1000	1000	ns
		4.5	500	500	500	
		6.0	400	400	400	

NOTE: Information on typical parametric values can be found in Chapter 4.

## FUNCTION TABLE

Operation	Inputs					Resulting Function			
	Reset	Serial Input A	Shift Clock	Latch Clock	Output Enable	Shift Register Contents	Latch Register Contents	Serial Output $SQ_H$	Parallel Outputs $Q_A-Q_H$
Reset shift register	L	X	X	L, H, ↘	L	L	U	L	U
Shift data into shift register	H	D	—	L, H, ↘	L	D → SRA; $SR_N \rightarrow SP_N + 1$	U	$SR_G \rightarrow SR_H$	U
Shift register remains unchanged	H	X	L, H, ↘	L, H, ↘	L	U	U	U	U
Transfer shift register contents to latch register	H	X	L, H, ↘	L, H, ↘	L	U	$SR_N \rightarrow LR_N$	U	$SR_N$
Latch register remains unchanged	X	X	X	L, H, ↘	L	*	U	*	U
Enable parallel outputs	X	X	X	X	L	*	**	*	Enabled
Force outputs into high-impedance state	X	X	X	X	H	*	**	*	Z

SR = shift register contents  
LR = latch register contentsD = data (L, H) logic level  
U = remains unchangedX = don't care  
Z = high impedance\* = depends on Reset and Shift Clock inputs  
\*\* = depends on Latch Clock input

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## PIN DESCRIPTIONS

## INPUTS

A (Pin 14) — Serial Data Input. The data on this pin is shifted into the 8-bit serial shift register.

## CONTROL INPUTS

Shift Clock (Pin 11) — Shift Register Clock Input. A low-to-high transition on this input causes the data at the Serial Input pin to be shifted into the 8-bit shift register.

Reset (Pin 10) — Active-low, Asynchronous, Shift Register Reset Input. A low on this pin resets the shift register portion of this device only. The 8-bit latch is not affected.

Latch Clock (Pin 12) — Storage Latch Clock Input. A low-to-high transition on this input latches the shift register data.

Output Enable (Pin 13) — Active-low Output Enable. A low on this input allows the data from the latches to be presented at the outputs. A high on this input forces the outputs ( $Q_A-Q_H$ ) into the high-impedance state. The serial output is not affected by this control input.

## OUTPUTS

 $Q_A-Q_H$  (Pins 15, 1, 2, 3, 4, 5, 6, 7) — Noninverted, 3-state, latch outputs. $SQ_H$  (Pin 9) — Noninverted, Serial Data Output. This is the output of the eighth stage of the 8-bit shift register. This output does not have three-state capability.

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## SWITCHING WAVEFORMS

FIGURE 1

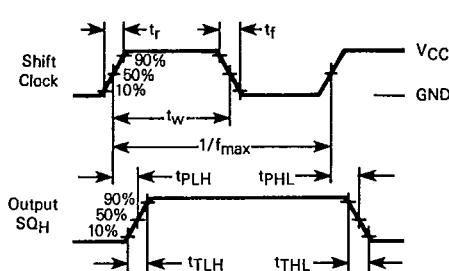


FIGURE 2

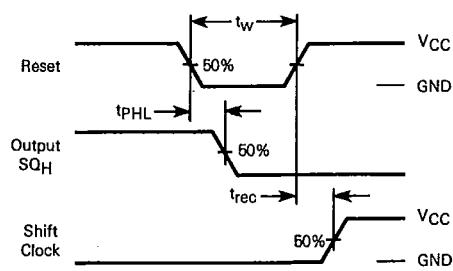


FIGURE 3

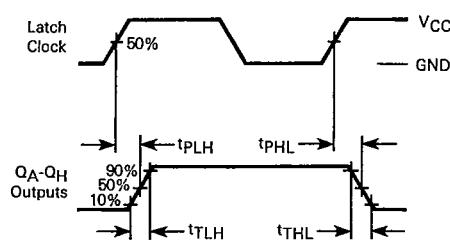
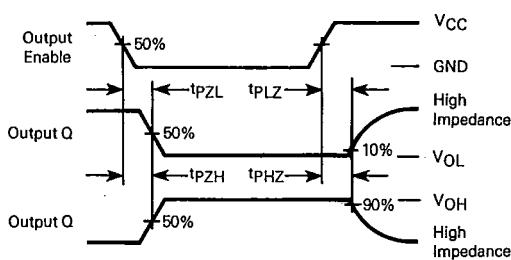


FIGURE 4



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FIGURE 5

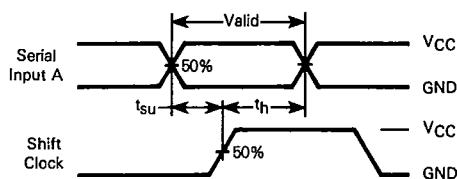


FIGURE 6

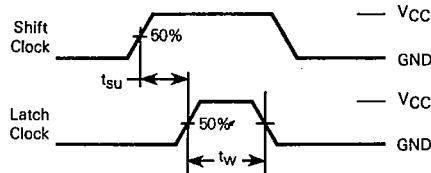
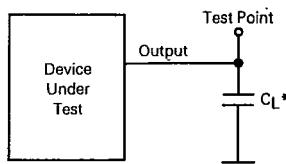
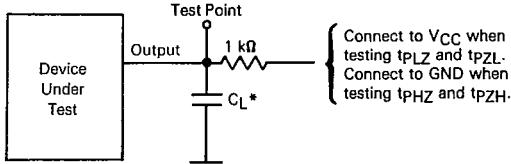


FIGURE 7 — TEST CIRCUIT



\* Includes all probe and jig capacitance.

FIGURE 8 — TEST CIRCUIT

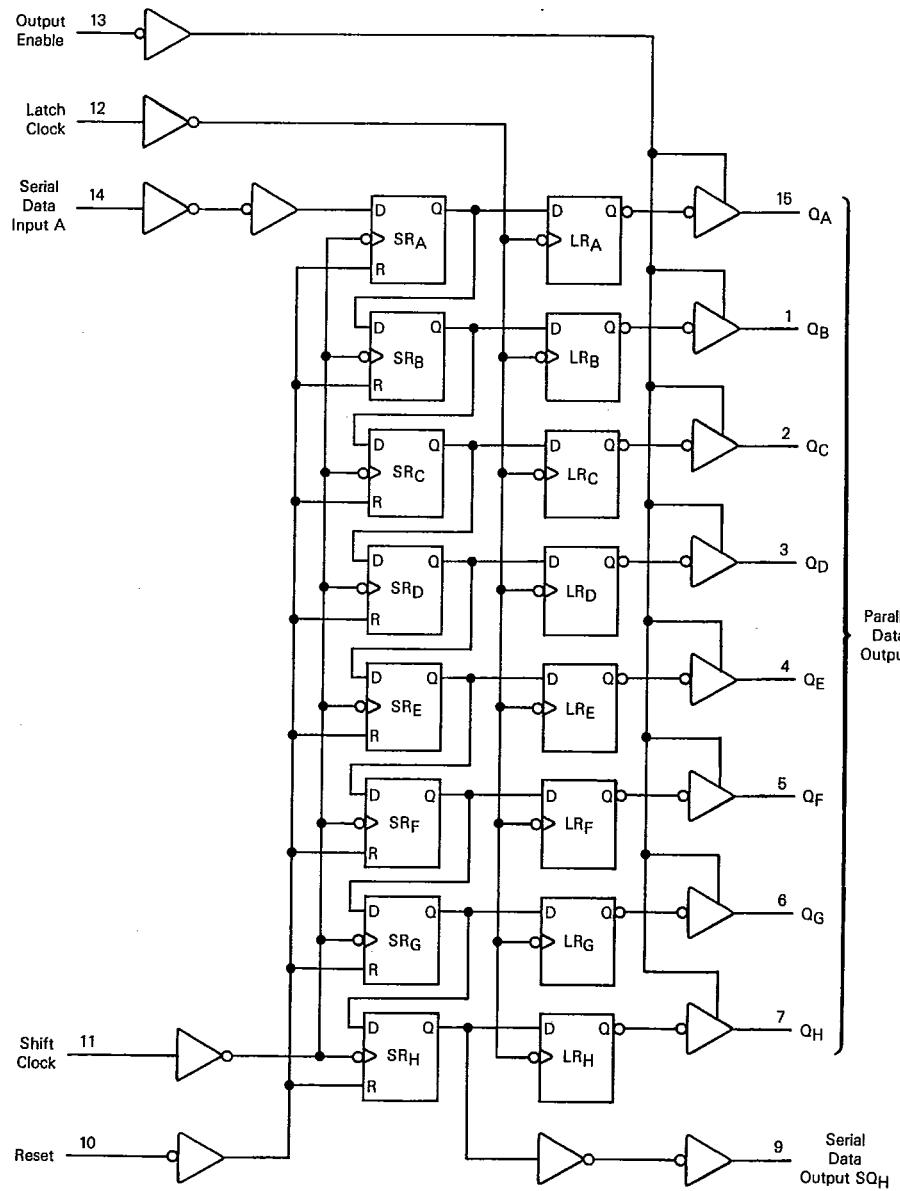


\* Includes all probe and jig capacitance.

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## EXPANDED LOGIC DIAGRAM

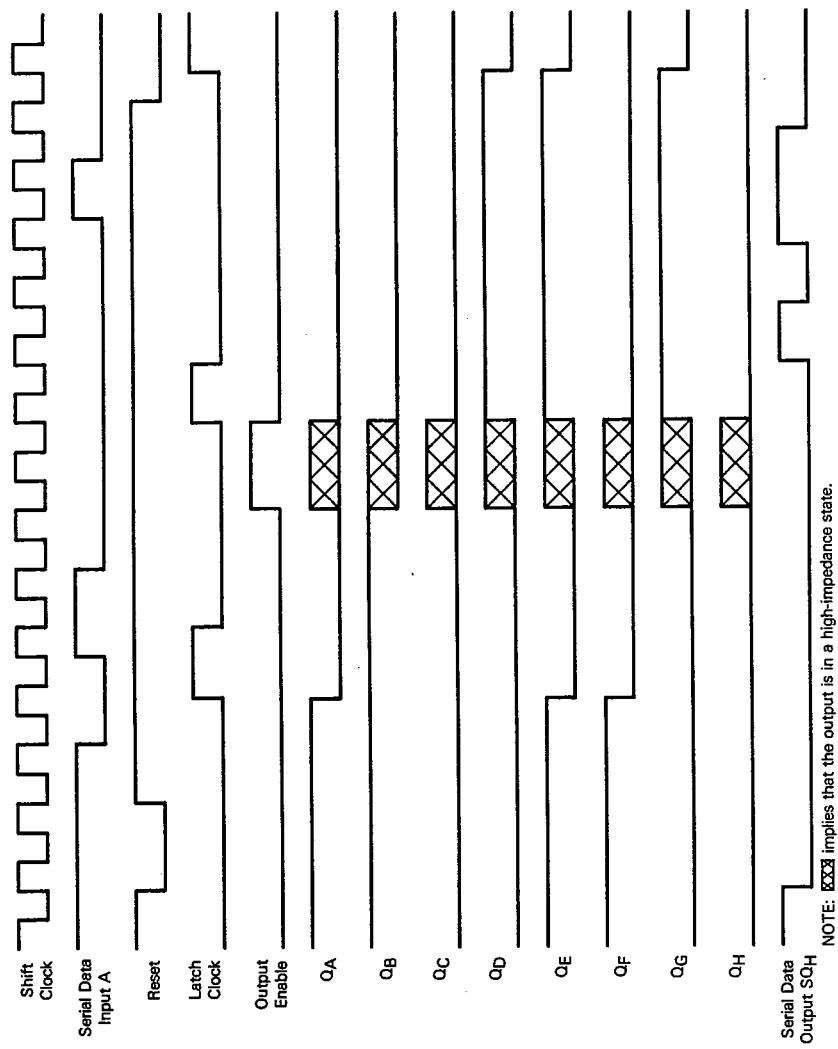


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## TIMING DIAGRAM



NOTE: implies that the output is in a high-impedance state.